

IN THE CLAIMS

Each claim of the present application is set forth below with a parenthetical notation immediately following the claim number indicating the current claim status. The Examiner's entry of the claim amendments, as shown in marked up form, under Section 1.121 is respectfully requested.

1. (WITHDRAWN) A process for controlling etching on a semiconductor substrate wherein the etching is affected by the concentration of an etchant gas, and wherein the etchant gas is input to an etch chamber via a mass flow controller, the process comprising:
 - determining a desired etchant gas concentration;
 - supplying an inert gas to the etch chamber;
 - producing a first signal representative of an actual etchant gas concentration;
 - producing a second signal representative of an inert gas concentration;
 - relating the first and the second signals to produce a normalized etchant gas concentration signal;
 - comparing the normalized etchant gas concentration signal with a signal representing the desired etchant gas concentration; and
 - controlling the mass flow controller in response to the comparing step.
2. (WITHDRAWN) The process of claim 1 wherein the etchant gas comprises an oxygen radical.
3. (WITHDRAWN) The process of claim 1 wherein the inert gas comprises argon.
4. (WITHDRAWN) The process of claim 1 wherein the etchant gas comprises an oxygen radical, the process further comprising:
 - supplying oxygen to the etch chamber, and
 - fanning a plasma within the etch chamber to form an oxygen radical from the oxygen.
5. (WITHDRAWN) The process of claim 1 wherein the first signal comprises a signal representative of a spectral emission line formed by the etchant gas.
6. (WITHDRAWN) The process of claim 1 wherein the second signal comprises a signal representative of a spectral emission line formed by the inert gas.

7. (WITHDRAWN) The process of claim 1 wherein the step of relating further comprises dividing the first signal by the second signal.

8. (WITHDRAWN) The process of claim 1 wherein the semiconductor substrate comprises a plurality of transistor gate features formed with predetermined dimensions, and wherein the etchant gas reduces certain feature dimensions.

9. (WITHDRAWN) The process of claim 1 wherein the step of relating comprises:
filtering the first signal to produce a filtered first signal representative of a spectral emission line formed by the etchant gas;

filtering the second signal to produce a filtered second signal representative of a spectral emission line formed by the inert gas; and

relating the first and the second filtered signals to produce the normalized etch gas concentration signal.

10. (WITHDRAWN) The process of claim 9 wherein the step of relating further comprises filtering the normalized etchant gas signal to remove short duration temporal variations.

11. (WITHDRAWN) The process of claim 10 where in the step of filtering further comprises integrating the normalized etchant gas signal.

12. (WITHDRAWN) The process of claim 1 wherein the first and the second signals comprise first and second optical signals, respectively.

13. (WITHDRAWN) The process of claim 12 further comprising filtering the first optical signal to produce a filtered first optical signal and transforming the filtered first optical signal to a first electrical signal, wherein the first electrical signal represents the actual etchant gas concentration.

14. (WITHDRAWN) The process of claim 12 further comprising filtering the second optical signal to produce a filtered second optical signal and transforming the filtered second optical signal to a second electrical signal, wherein the second electrical signal represents the inert gas concentration.

15. (WITHDRAWN) A process for controlling isotropic etching on a semiconductor substrate wherein the isotropic etching is affected by a concentration of an etchant gas input to an etch chamber via a mass flow controller, and wherein anisotropic etching also occurs in the etch chamber, the process comprising:

determining a desired etchant gas concentration;
supplying a passivating gas to the etch chamber;
producing a first signal representative of an actual etchant gas concentration; producing a second signal representative of a passivating gas concentration;
relating the first and the second signals to produce a third signal;
comparing the third signal with a predetermined reference; and
controlling the concentration of at least one of the etchant gas and the passivating gas in response to the comparing step.

16. (WITHDRAWN) The process of claim 15 wherein the third signal represents a ratio of the etchant gas and the passivating gas.

17. (WITHDRAWN) The process of claim 15 wherein the first signal comprises a signal representative of a spectral emission line formed by the etchant gas.

18. (WITHDRAWN) The process of claim 15 wherein the second signal comprises a signal representative of a spectral emission line formed by the passivating gas.

19. (WITHDRAWN) The process of claim 15 wherein the reference relates to the ratio of the passivating gas to the etchant gas to limit an extent of the anisotropic etch.

20. (WITHDRAWN) A process for controlling an etch rate on a semiconductor substrate wherein the etch rate is substantially affected by the concentration of an etchant gas, and wherein the etchant gas is input to an etch chamber via a mass flow controller, the process comprising:

determining the etchant gas concentration in the etch chamber;
comparing the concentrations with a target value;
generating an error signal in response to the comparing step; and
controlling the mass flow controller in response to the error signal.

21. (CURRENTLY AMENDED) An apparatus for ~~controlling an etch-trim process~~ duration trim etching a structure on a semiconductor substrate, ~~the trim etching employing~~ wherein the etch-trim process duration is affected by a concentration of an etchant gas, and ~~wherein the an etchant gas supplied is input to an etch chamber via a first mass flow controller,~~ and wherein an etchant gas supplied is input to an etch chamber via a first mass flow controller, ~~and wherein an inert gas supplied is input to the etch chamber via a second mass flow controller,~~ the apparatus comprising:

a first optical device for producing a first signal representative of an etchant gas concentration, wherein the first signal is based on an emissive spectral line for the etchant gas;

a second optical device for producing a second signal representative of an inert gas concentration, wherein the second signal is based in an emissive spectral line for the inert gas, wherein the emissive spectral line for the etchant gas and the emissive spectral line for the inert gas exhibit similar cross-sections for excitation;

an element for relating the first and the second signals to produce a normalized etchant gas concentration signal; and

a comparing element for comparing the normalized etchant gas concentration signal with a signal representing a desired constant etchant gas concentration to maintain a consistent etch trim rate within the chamber and a determinable etch trim duration, after which the etch trim process is terminated, the comparing element and for producing a normalized signal in response thereto, the normalized signal provided to the first mass flow controller for providing a substantially constant etchant gas concentration, ~~during the etch trim process, thereby resulting in a determinable etch trim process duration.~~

22. (ORIGINAL) The apparatus of claim 21 wherein the etchant gas comprises an oxygen radical.

23. (ORIGINAL) The apparatus of claim 21 wherein the inert gas comprises argon.

24. (ORIGINAL) The apparatus of claim 21 further comprising an energy source for forming a plasma in the etch chamber.

25. (ORIGINAL) The apparatus of claim 24 wherein the first signal comprises a first signal representative of a spectral emission line formed by the etchant gas interacting with the plasma.

26. (ORIGINAL) The apparatus of claim 24 wherein the second signal comprises a second signal representative of a spectral emission line formed by the inert gas interacting with the plasma.

27. (ORIGINAL) The apparatus of claim 21 wherein the element for relating the first and the second signals comprises a divider.

28. (ORIGINAL) The apparatus of claim 21 wherein the first optical device comprises in serial relation, an optical fiber disposed to receive light energy from within the etch chamber, an optical filter and a light detector for producing the first signal.

29. (ORIGINAL) The apparatus of claim 21 wherein the second optical device comprises in serial relation, an optical fiber disposed to receive light energy from within the etch chamber, an optical filter and a light detector for producing the second signal.

30. (ORIGINAL) The apparatus of claim 21 wherein the first and the second optical devices are responsive to a bifurcated optical fiber disposed within an opening in the etch chamber and responsive to spectral emissions in the etch chamber, wherein the optical fiber carries an optical signal representative of the actual etchant gas concentration and the inert gas concentration.